IN THE CLAIMS:

1-28. (canceled).

- 29. (Amended) An in-plane switching liquid crystal display device comprising:
 - a first substrate and a second substrate;
 - a gate line and a common line on the first substrate;
 - a data line perpendicular to the gate line;
- a thin film transistor at a crossing point of the gate and data lines; the thin film transistor including a source electrode, a drain electrode and a gate electrode;
 - a first insulating layer over the gate line;
 - a second insulating layer of an organic material over the first substrate;

pixel electrodes on the second insulating layer;

common electrodes on the second insulating layer, wherein the common electrodes and the pixel electrodes form an alternating pattern, the common electrodes including an outermost common electrode adjacent to the data line; and

a liquid crystal layer between the first and second substrates,

wherein the outermost common electrode and the data line are on different layers and wherein a portion of the outermost common electrode overlaps the data line.

- 30. (Original) The in-plane switching liquid crystal display device of claim 29, wherein the pixel electrodes are transparent.
- 31. (Amended) The in-plane switching liquid crystal display device of claim 30, wherein the pixel electrodes are formed of a material selected from the group consisting of indium tin oxide (ITO) and indium zinc oxide (IZO).

32. (Original) The in-plane switching liquid crystal display device of claim 29, wherein the common electrodes are transparent.

- 33. (Amended) The in-plane switching liquid crystal display device of claim 32, wherein the common electrodes are formed of a material selected from the group consisting of indium tin oxide (ITO) and indium zinc oxide (IZO).
- 34. (Original) The in-plane switching liquid crystal display device of claim 29, further comprising an auxiliary common electrode on the second insulating layer, the auxiliary common electrode contacting respective first ends of the common electrodes and contacting the common line via a contact hole through the first and second insulating layers.
- 35. (Original) The in-plane switching liquid crystal display device of claim 29, further comprising an auxiliary pixel electrode contacting the pixel electrodes.
- 36. (Original) The in-plane switching liquid crystal display device of claim 29, further comprising a capacitor electrode electrically connected with the pixel electrodes.
- 37. (Amended) A method of fabricating an in-plane switching liquid crystal display device, comprising:

depositing and patterning a first metal on a first substrate to form a gate line and a common line on the first substrate, the gate line including a gate electrode;

forming a first insulating layer over the gate line;

forming an active layer on the first insulating layer;

depositing and patterning a second metal on the first insulating layer to form a data line perpendicular to the gate line and source and drain electrodes;

forming a second insulating layer of an organic material over the first insulating layer, the second metal and the active layer, the second insulating layer having a contact hole;

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depositing and patterning a conductive material on the second insulating layer to form pixel electrodes and common electrodes on the second insulating layer, wherein the common electrodes include an outermost common electrode adjacent to the data line; and

interposing a liquid crystal layer between the first substrate and a second substrate, wherein the outermost common electrode and the data line are on different layers and wherein a portion of the outermost common electrode overlaps the data line.

- 38. (Original) The method of fabricating an in-plane switching liquid crystal display device of claim 37, wherein the common electrodes and the pixel electrodes form an alternating pattern.
- 39. (Original) The method of fabricating an in-plane switching liquid crystal display device of claim 37, wherein the pixel electrodes are transparent.
- 40. (Amended) The method of fabricating an in-plane switching liquid crystal display device of claim 39, wherein the pixel electrodes are formed of a material selected from the group consisting of indium tin oxide (ITO) and indium zinc oxide (IZO).
- 41. (Original) The method of fabricating an in-plane switching liquid crystal display device of claim 37, wherein the common electrodes are transparent.
- 42. (Amended) The method of fabricating an in-plane switching liquid crystal display device of claim 41, wherein the common electrodes are formed of a material selected from the group consisting of indium tin oxide (ITO) and indium zinc oxide (IZO).

- 43. (Original) The method of fabricating an in-plane switching liquid crystal display device of claim 37, further comprising forming an auxiliary electrode on the second insulating layer, the auxiliary electrode contacting one of the source and drain electrodes through a contact hole.
- 44. (Original) The method of fabricating an in-plane switching liquid crystal display device of claim 37, further comprising forming an auxiliary common electrode on the second insulating layer, the auxiliary common electrode contacting respective first ends of the common electrodes and contacting the common line via a contact hole through the first and second insulating layers.
- 45. (Original) The method of fabricating an in-plane switching liquid crystal display device of claim 37, further comprising forming an auxiliary pixel electrode contacting the pixel electrodes.
- 46. (Original) The method of fabricating an in-plane switching liquid crystal display device of claim 37, further comprising forming a capacitor electrode electrically connected with the pixel electrodes.
- 47. (Amended) An in-plane switching liquid crystal display device, comprising:
 - a first substrate and a second substrate;
 - a gate line and a common line on the first substrate;
 - a data line perpendicular to the gate line;
 - a thin film transistor including a source electrode, a drain electrode and a gate electrode;
- an insulating layer on the thin film transistor, the insulating layer having a contact hole above one of the source electrode and the drain electrode;
 - a plurality of common electrodes on the insulating layer;
 - a plurality of pixel electrodes on the insulating layer; and
- an auxiliary electrode contacting the one of the source electrode and the drain electrode through the contact hole.